

Description

The HXY70P03D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

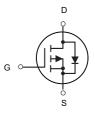


TO-252-2L

General Features

 $V_{DS} = -30V I_{D} = -70 A$

 $R_{DS(ON)} < 10 m\Omega$ @ V_{GS} =-10V



Application

Battery protection

Load switch

Uninterruptible power supply

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY70P03D	TO252-2L	70P03 XXX YYYY	2500

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	-30	V	
Vgs	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ^{1,6}	-70	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ^{1,6}	Continuous Drain Current, V _{GS} @ -10V ^{1,6} -50		
Ірм	Pulsed Drain Current ²	Pulsed Drain Current ² -200		
EAS	Single Pulse Avalanche Energy ³	lse Avalanche Energy ³ 80		
las	Avalanche Current	-40	А	
P _D @T _C =25°C	Total Power Dissipation ⁴	90	W	
Тѕтс	Storage Temperature Range	-55 to 175	°C	
TJ	Operating Junction Temperature Range	-55 to 175	°C	
R ₀ JA	Thermal Resistance Junction-ambient ¹(t≦10S)	20	°C/W	
	Thermal Resistance Junction-ambient ¹(Steady State)	50	°C/W	
Rejc	Thermal Resistance Junction-case ¹	1.6 °C/W		



Electrical Characteristics (T_J=25 ° C , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			٧
		V _{GS} =-10V , I _D =-20A		7	10	mΩ
Rds(on)	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V , I _D =-15A		11	18	mΩ
V _G S(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2		-2.5	V
		V _{DS} =-24V , V _{GS} =0V , T _J =25°C			-1	
loss	Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =55°C		-5	uA	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.2		Ω
Qg	Total Gate Charge (-10V)			60		nC
Qgs	Gate-Source Charge	V _{DS} =-15V , V _{GS} =-10V		9		
Qgd	Gate-Drain Charge	I _D =-18A		15		
Td(on)	Turn-On Delay Time			17		
Tr	Rise Time	V _{DD} =-15V V _{GS} =-10V		40		ns
Td(off)	Turn-Off Delay Time	$R_G=3.3\Omega$,		55		
T _f	Fall Time	I _D =-20A		13		
Ciss	Input Capacitance			3450		
Coss	Output Capacitance	V _{DS} =-25V , V _{GS} =0V , f=1MHz		255		pF
Crss	Reverse Transfer Capacitance			140		
Is	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current			-70	Α
Vsp	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.2	V
trr	Reverse Recovery Time	IF=-20A , di/dt=100A/µs ,		22		nS
Q _{rr}	Reverse Recovery Charge	—T _J =25°C		72		nC

Note:

^{1.}The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

^{2.}The data tested by pulsed , pulse width $\,\leq\,300\text{us}$, duty cycle $\,\leq\,2\%$

^{3.} The EAS data shows Max. rating . The test condition is V_{DD} =-50V, V_{GS} =-10V, L=0.1mH, I_{AS} =-40A

^{4.}The power dissipation is limited by 150°C junction temperature

^{5.}The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation

^{6.} The maximum current rating is package limited.



Typical Characteristics

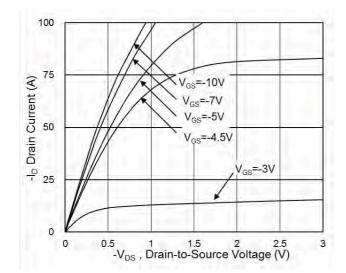


Fig.1 Typical Output Characteristics

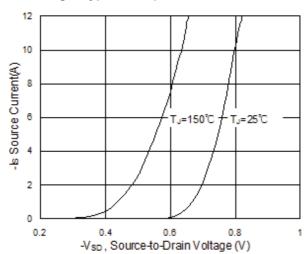


Fig.3 Forward Characteristics of Reverse

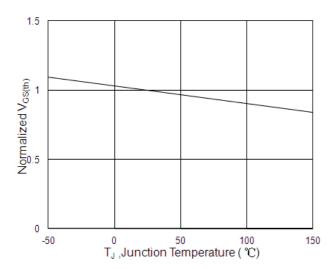


Fig.5 Normalized -V_{GS(th)} vs. T_J

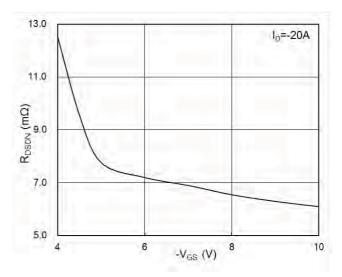


Fig.2 On-Resistance vs. Gate-Source Voltage

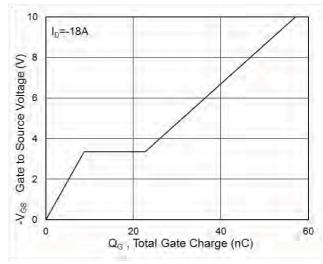


Fig.4 Gate-Charge Characteristics

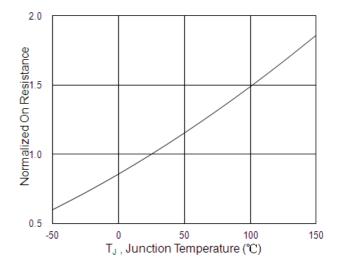
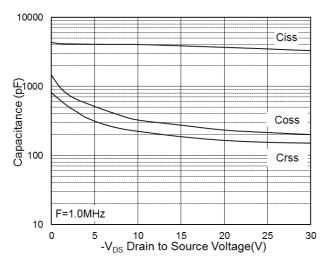


Fig.6 Normalized R_{DSON} vs. T_J





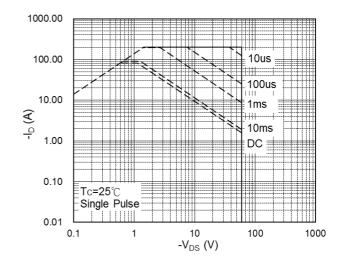


Fig.7 Capacitance

Fig.8 Safe Operating Area

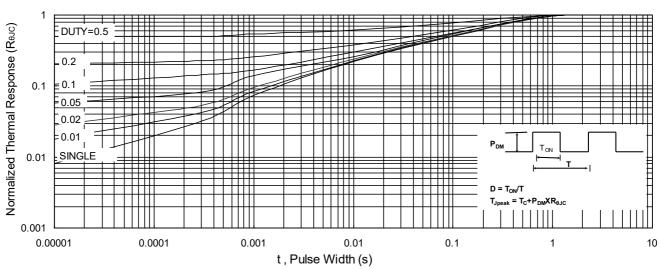


Fig.9 Normalized Maximum Transient Thermal Impedance

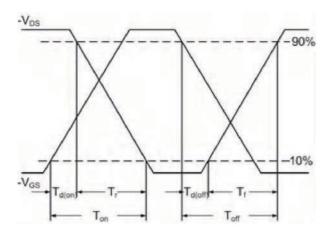


Fig.10 Switching Time Waveform

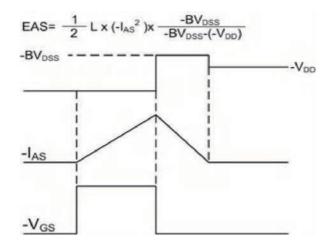
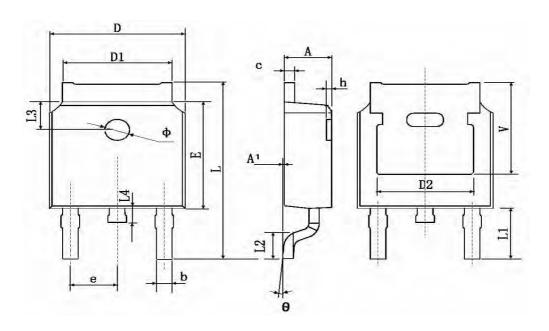


Fig.11 Unclamped Inductive Switching Waveform



TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
Α	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830 TYP.		0.190 TYP.			
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3) TYP.	0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			

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